ShiLing® 浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

产品规格书

Specifcation of products

产品名称:三相整流桥

产品型号:MDS60A-H1

浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

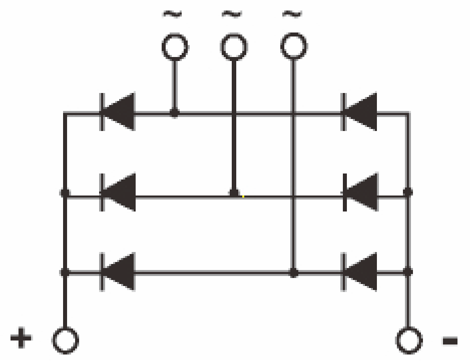
地址：浙江省 丽水市 莲都区
电话：（0578）3012571 3615078
传真：（0578）3611180
邮编： 323000
E-mail:smrshiling01@163.com
Http//www.smrshiling.com

拟制	审核	核准
林益龙	曹剑龙	宗瑞

版本号：05 更新日期：2023.8

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j(℃)	VALUE			UNIT
				Min	Type	Max	
I_O	DC output current	Three-phase full wave rectifying circuit, T_C=100℃	150		60		A
V_{RRM}	Repetitive peak reverse voltage	V_{RRM} tp=10ms V_{RsM}= V_{DRM}&V_{RRM}+200V	150	600		1800	V
I_{RRM}	Repetitive peak current	at V_{RRM}	150			5	mA
I_{FSM}	Surge forward current	10ms half sine wave V_R=0.6V_{RRM}	150			0.46	KA
I^2t	I^2T for fusing coordination					1.05	A^2s*10^3
V_{FO}	Threshold voltage		150			0.80	V
r_F	Forward slop resistance					3.0	mΩ
V_{FM}	Peak for ward voltage	I_{FM}=150A	25			1. 3	V
$R_{th(j-c)}$	Thermal resistance Junction to heatsink	Single side cooled				1.45	℃ /W
V_{iso}	Isolation voltage	50Hz,R.M.S,t=1min,I_{iso}:1mA(max)		3000			V
F_m	Terminal connection torque(M5)				4.0		N.m
	Mounting torque(M6)				5.0		N.m
T_{stg}	Stored temperature			-40		150	℃
W_t	Weight				175		g
Outline							

OUTLINE DRAWING & CIRCUIT DIAGRAM



Rating and Characteristic

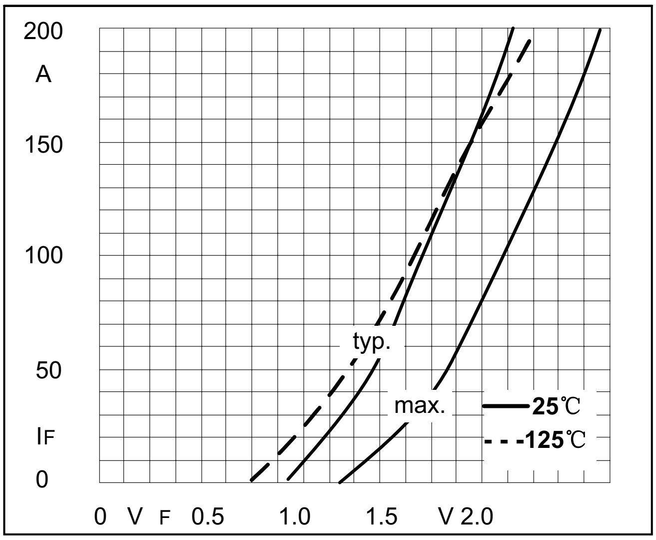


Fig1. Forward Characteristics

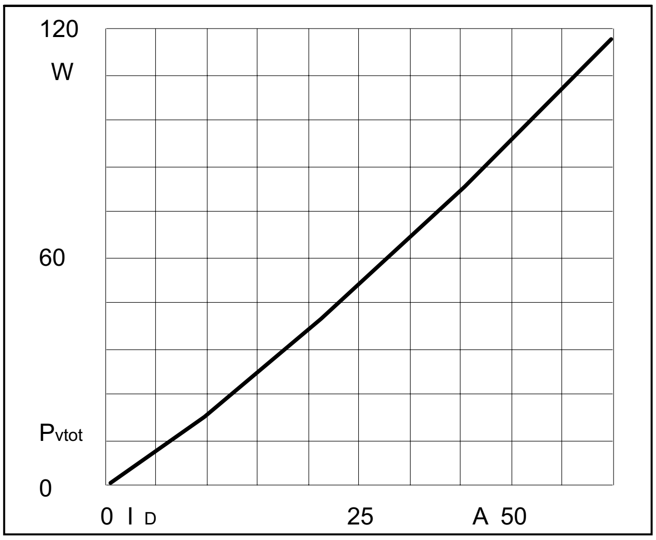


Fig2.Power dissi pation

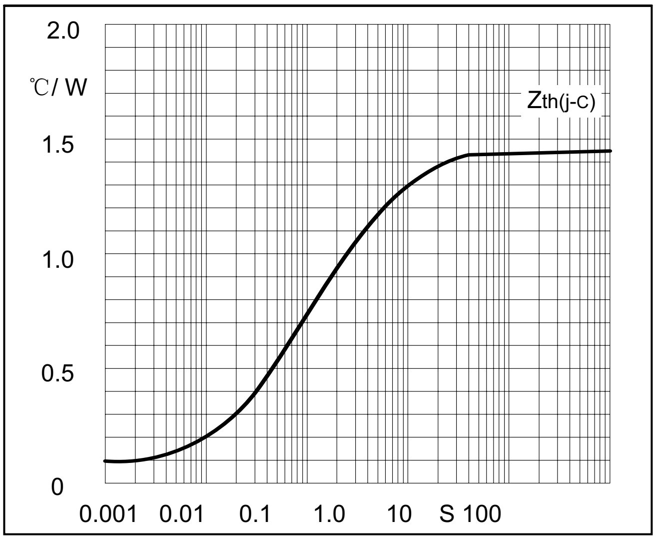


Fig3. Transient thermal impedance

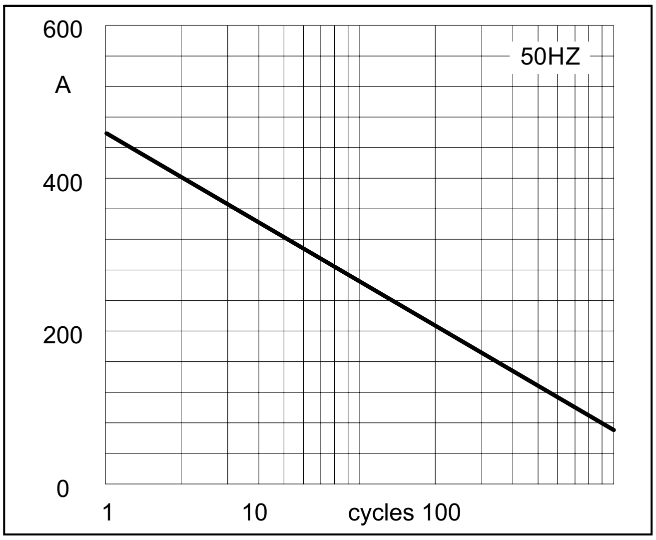


Fig4. Max Non-Repetitive Forward Surge Current

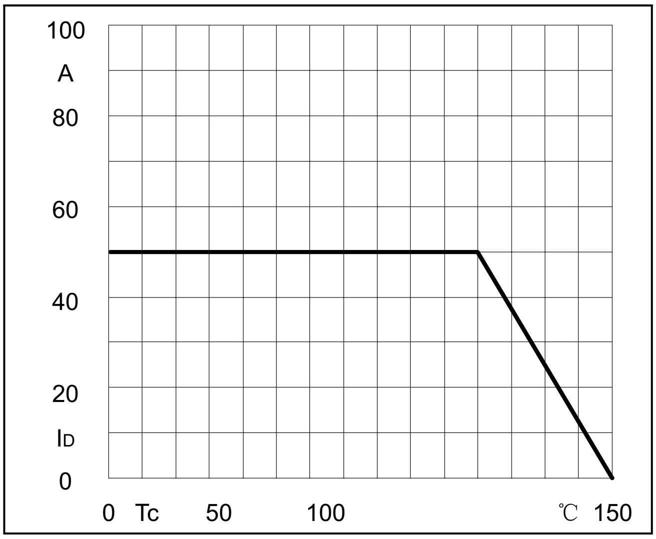
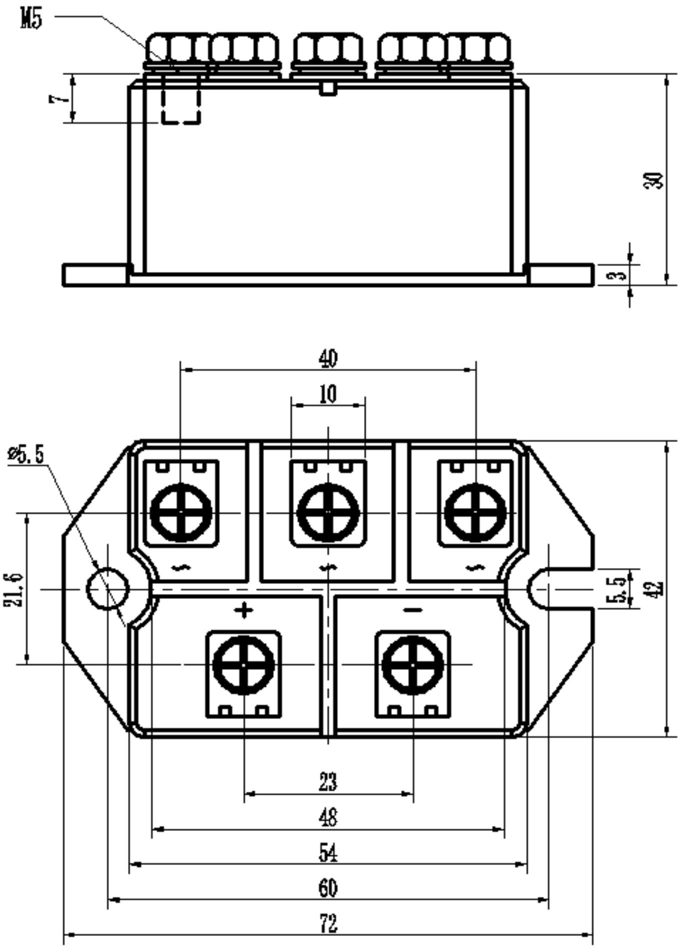


Fig5.Forward Current Derating Curve

Package Outline Information



Dimensions in mm